

# 2SB0928 (2SB928), 2SB0928A (2SB928A)

www.panasonic.com Silicon PNP epitaxial planar type

For Power amplification

For TV vertical deflection output

Complementary to 2SD1250 and 2SD1250A

## ■ Features

- High collector-emitter voltage (Base open)  $V_{CEO}$
- High collector power dissipation  $P_C$
- N type package enabling direct soldering of the radiating fin to the printed circuit board, etc. of small electronic equipment.

## ■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

Parameter		Symbol	Rating	Unit
Collector-base voltage (Emitter open)		V <sub>CBO</sub>	−200	V
Collector-emitter voltage (Base open)	2SB0928 2SB0928A	V <sub>CEO</sub>	−150 −180	V
Emitter-base voltage (Collector open)		V <sub>EBO</sub>	−6	V
Collector current		I <sub>C</sub>	−2	A
Peak collector current		I <sub>CP</sub>	−3	A
Collector power dissipation	T <sub>a</sub> = 25°C	P <sub>C</sub>	30 1.3	W
Junction temperature		T <sub>J</sub>	150	°C
Storage temperature		T <sub>stg</sub>	−55 ~ +150	°C

## ■ Electrical Characteristics $T_C = 25^\circ\text{C} \pm 3^\circ\text{C}$

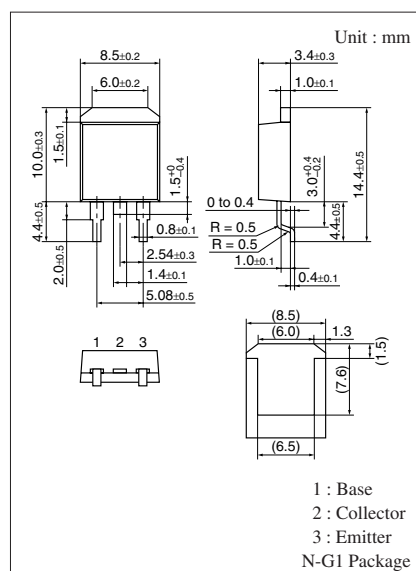
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = -500 \mu\text{A}$ , $I_E = 0$	-200			V
Collector-emitter voltage (Base open)	2SB0928 $V_{CEO}$	$I_C = -5 \text{ mA}$ , $I_B = 0$	-150			V
	2SB0928A		-180			
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = -500 \mu\text{A}$ , $I_C = 0$	-6			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = -200 \text{ V}$ , $I_E = 0$			-50	$\mu\text{A}$
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = -4 \text{ V}$ , $I_C = 0$			-50	$\mu\text{A}$
Forward current transfer ratio	$h_{FE1}^*$	$V_{CE} = -10 \text{ V}$ , $I_C = -150 \text{ mA}$	60		240	—
	$h_{FE2}$	$V_{CE} = -10 \text{ V}$ , $I_C = -400 \text{ mA}$	50			
Base-emitter voltage	$V_{BE}$	$V_{CE} = -10 \text{ V}$ , $I_C = -400 \text{ mA}$			-1.0	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500 \text{ mA}$ , $I_B = -50 \text{ mA}$			-1.0	V
Transition frequency	$f_T$	$V_{CE} = -10 \text{ V}$ , $I_C = -0.5 \text{ A}$ , $f = 10 \text{ MHz}$		40		MHz

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

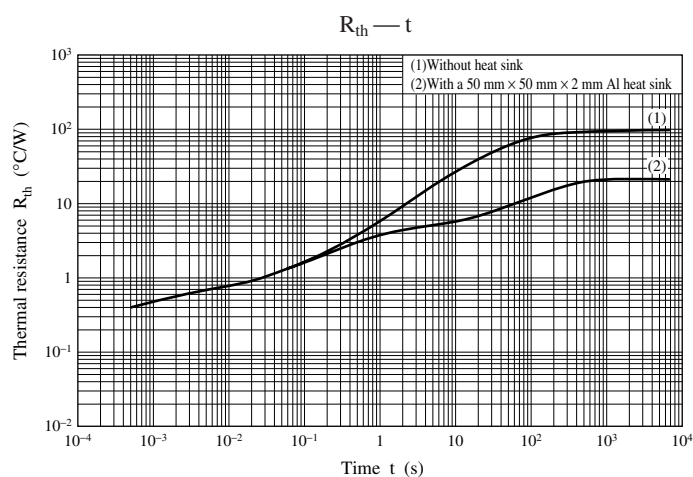
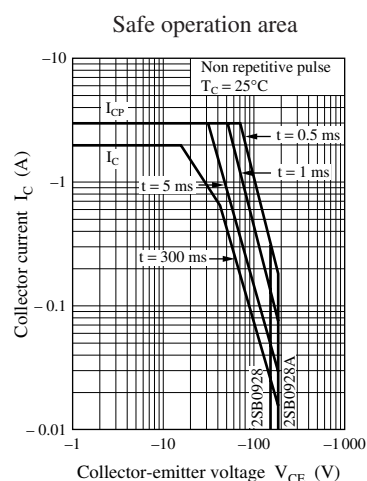
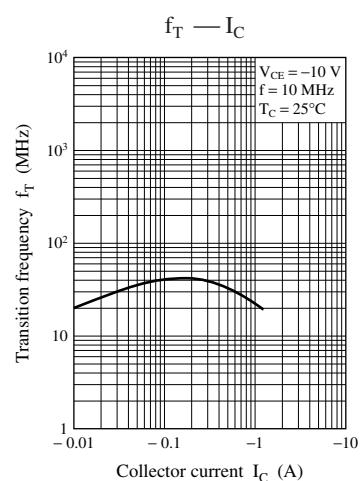
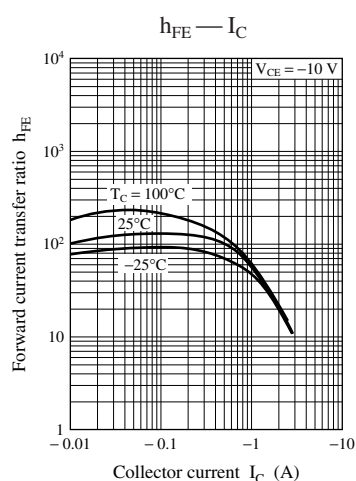
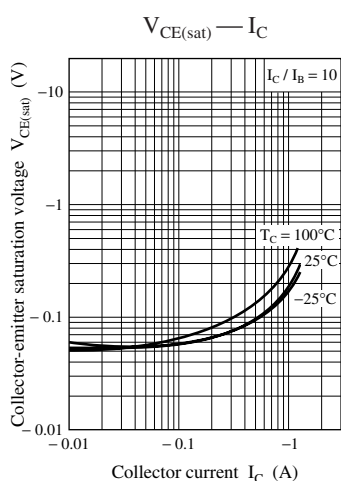
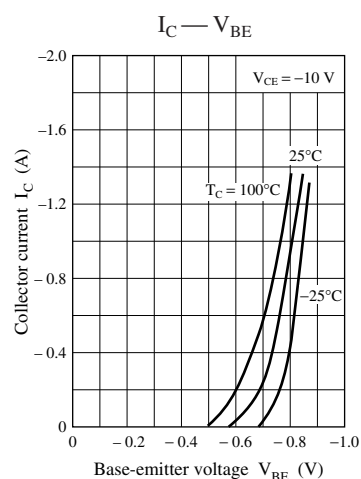
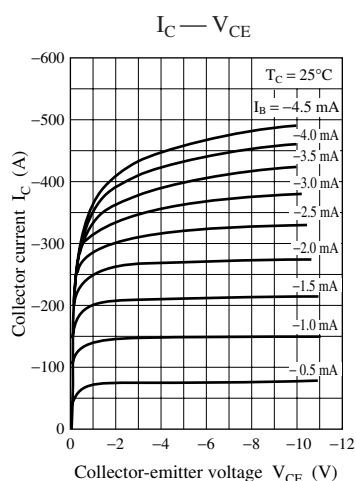
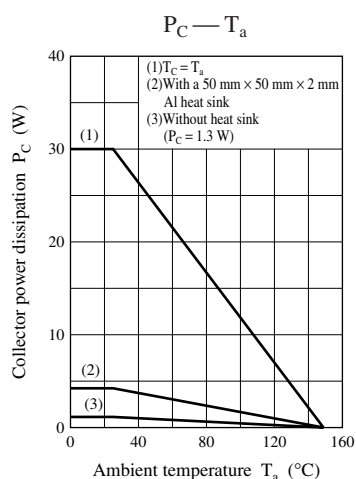
2. \*: Rank classification

Rank	Q	P
$h_{FE1}$	60 to 140	100 to 240

Note) The part numbers in the parenthesis show conventional part number.



Note) Self-supported type package is also prepared



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